Silicon Bridge Rectifiers **_GBS4A--GBS4M_**

FEATURES

Lead-free

- Rating to 1000V PRV
- Surge overload rating to 120 Amperes peak
- Reliable low cost construction utilizing molded plastic technique results in inexpensive product
- Lead solderable per MIL-STD-202 method 208

Maximum Ratings(@TA = 25°C unless otherwise specified)

Characteristic	Symbol	GBS 4A	GBS 4B	GBS 4D	GBS 4G	GBS 4J	GBS 4K	GBS 4M	UNITS
Maximum recurrent peak reverse voltage	V_{RRM}	50	100	200	400	600	800	1000	V
Maximum RMS voltage	V_{RMS}	35	70	140	280	420	560	700	V
Maximum DC blocking voltage	V_{DC}	50	100	200	400	600	800	1000	V
50Hz sine wave, R-load Without heat sink Ta=25℃ 50Hz sine wave, R-load With heat sink Tc=50℃	$I_{F(AV)}$	1.5 4.0							A
Peak forward surge current 8.3ms single half-sine-wave superimposed on rated load	I_{FSM}	120							A

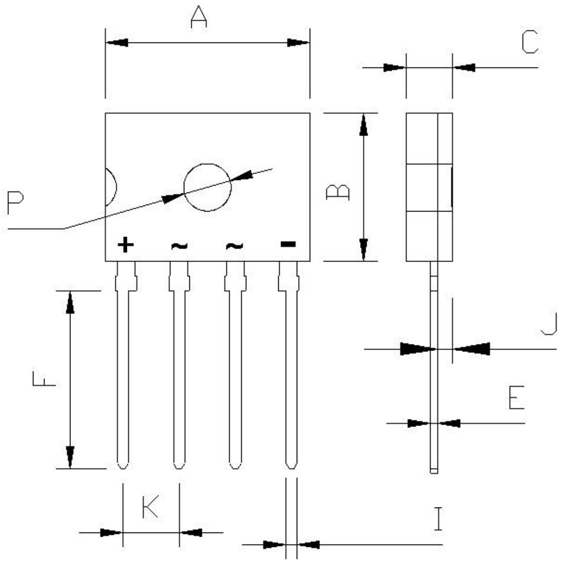
Thermal Characteristics

Characteristic	Symbol	Value	UNITS
Operating junction temperature range	T_J	- 55 ---- + 150	℃
Storage temperature range	T_{STG}	- 55 ---- + 150	℃

Electrical Characteristics (@TA = 25°C unless otherwise specified)

Characteristic	Symbol	Value	UNITS
Maximum instantaneous forward voltage @2.0A	V_F	1.05	V
Maximum reverse current @T_A=25 ℃ at rated DC blocking voltage @T_A=100℃	I_R	5.0 500	μ A

PACKAGE OUTLINE DIMENSIONS



GBS		
Dim	Min	Max
A	13.65	14.15
B	9.80	10.20
C	2.95	3.25
E	0.35	0.65
F	11.70	12.30
I	0.65	0.95
J	0.90	1.20
K	3.60	4.00
P	Ø3.2Typical	
All Dimensions in mm		

Silicon Bridge Rectifiers

GBS4A--GBS4M

FIG.1 – TYPICAL FORWARD CURRENT DERATING CURVE

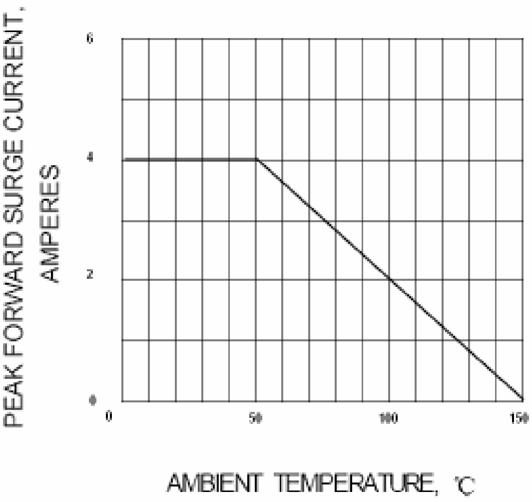


FIG.2 – MAXIMUM FORWARD SURGE CURRENT

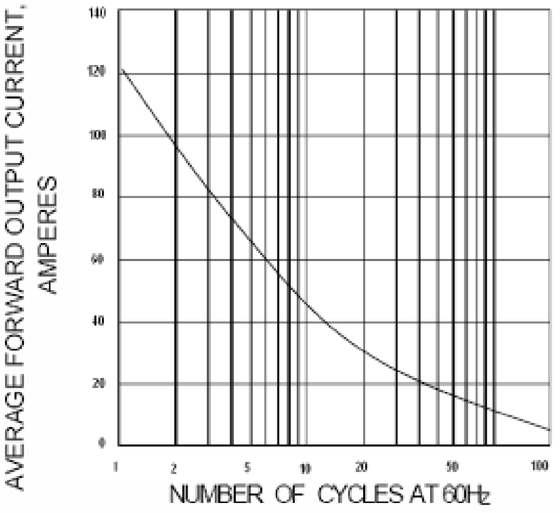


FIG.3 – TYPICAL FORWARD CHARACTERISTIC

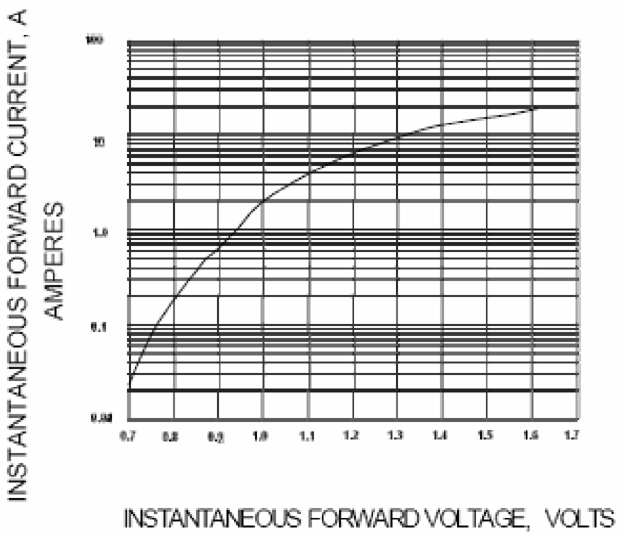


FIG.4 – TYPICAL REVERSE CHARACTERISTIC